

a film forming chamber for forming a thin film on the substrate by a CVD method under the reduced pressure; and

a transferring mechanism for receiving the dried substrate from the drying chamber through the second transferring port and for transferring the received substrate to the film forming chamber under the reduced pressure.

5. (amended) The apparatus as set forth in claim 1, further comprising:

a conductive film forming chamber for forming a conductive film on the substrate formed with an insulating film having a recessed portion in a front face thereof so that the recessed portion is embedded with the conductive film;

wherein the substrate formed with the conductive film in the conductive film forming chamber is polished in the polishing chamber so that the conductive film formed on the front face of the insulating film except for the recessed portion is polished away.

9 (amended) A method, comprising the steps of:

polishing a conductive film which is formed on the substrate;

cleaning and drying the polished substrate under a reduced pressure; and

transferring the substrate to a position for forming a thin film by a CVD method performed under the reduced pressure and forming the thin film at the position while maintaining the reduced-pressure state.

10. (amended) The method as set forth in claim 9, further comprising the step of:

forming the conductive film on the substrate on which an insulating film having a recessed portion on a front face thereof is formed before the polishing step so that the recessed portion is embedded with the conductive film.

12 (amended) An apparatus, comprising:

a first substrate carrier for transferring a substrate in an atmospheric air;

a first substrate processing portion performing a vacuum type processing on the substrate;

a second substrate processing portion performing a solution type processing on the substrate;

a first delivering and receiving portion delivering and receiving the substrate having a relation to the solution type processing between the second substrate processing portion and the first substrate processing portion; and

a second delivering and receiving portion delivering and receiving the substrate having no relation to the solution type processing between the first substrate transferring portion and the first substrate processing portion.

13. (amended) The apparatus as set forth in claim 12,
wherein the first substrate processing portion has a CVD film forming chamber.

14. (amended) The apparatus as set forth in claim 12,
wherein the first substrate processing portion has an etching processing chamber.

15. (amended) The apparatus as set forth in claim 12,
wherein the first substrate processing portion has a resist removing chamber.

16. (amended) The apparatus as set forth in claim 12,
wherein the first substrate delivering and receiving portion has a mechanism of drying the substrate under a reduced pressure.

17. (amended) The apparatus as set forth in claim 12, further comprising:
a second substrate carrier perpendicularly connected to the first substrate carrier and also connected to the first substrate delivering and receiving portion for transferring the substrate in an atmospheric air;

a polishing chamber disposed along the second substrate carrier, for polishing the substrate; and

a cleaning chamber disposed along the second substrate carrier for cleaning the polished substrate.

18. (amended) The apparatus as set forth in claim 17, further comprising: